Applic. No. 10/608,620 Prel. Amdt. dated 12/17/03

Amendments to the Specification:

Please replace the paragraph on page 1, lines 8-13, with:

The present patent application relates to methods for

producing a thermoelectric layer structure on a substrate with

at least one electrically anisotropicallyt anisotropically

conductive V-VI layer, in particular a (Bi, Sb)₂ (Te, Se)₃

layer and to components incorporating such a thermoelectric

layer structure.

Please replace the paragraph on page 2, lines 24-26, with:

d) Venkatasubbramanian Venkatasubramanian, R. et al., titled
"Thin-film Thermoelectric Devices With High Room-Temperature
Figs. Figures Of Merit", Nature, Vol. 43, 11. Oct. 2001, pp.
597-602.

Please replace the paragraph on page 3, lines 11-17, with:
What is disadvantageous in the case of the known solutions is
that thermoelectric components currently cannot be grown in a
uniquely an uniquely oriented manner (e.g. with the c-axis
parallel to the substrate surface) on customary substrates
using thin-film methods. It is an aim of the invention to
uniquely set the known anisotropy of the V-VI materials in an
advantageous manner for the construction of components.

Please replace the paragraph on page 7, lines 10-19, with:

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In this case, for the crystallographic orientation of thermoelectric layers during growth in thin-film processes, preferably during sputtering, an additional electric field is applied to the substrate electrode during the sputtering operation. This results in preferred growth orientation in the direction of maximum electrical conductivity. This is important e.g. in the case of \$\frac{\text{Bi}_2\text{Te}_3}{2}\$ (\text{Bi},\text{Sb})_2(\text{Te},\text{Se})_3 \text{ or V-VI-materials} owing to its anisotropic thermoelectric properties. The growth orientation in the direction of the preferred a-axis becomes important as a result of the additional electric field.

Please replace the paragraph on page 10, lines 22-26, with:

Directed growth succeeds with an electromechanical

electrochemical starting layer, which grows in the direction

of highest conductivity (a-plane of Bi₂Te₃) perpendicular to

specific substrates while complying with specific experimental

conditions. This is known from the following publications by: